

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

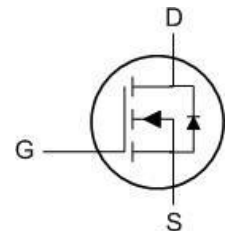
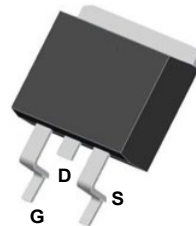


BVDSS	RDSON	ID
150V	4mΩ	180A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

TO263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	200	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	125	A
I_{DM}	Pulsed Drain Current ²	800	A
EAS	Single Pulse Avalanche Energy ³	1155	mJ
I_{AS}	Avalanche Current	68	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	338	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.38	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	150	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=90A$	---	4	4.8	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	3	4	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=150V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=150V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V$, $I_D=90A$	---	145.7	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4	---	Ω
Q_g	Total Gate Charge	$V_{DS}=75V$, $V_{GS}=10V$, $I_D=90A$	---	19.9	---	nC
Q_{gs}	Gate-Source Charge		---	32.1	---	
Q_{gd}	Gate-Drain Charge		---	19	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DD}=75V$, $R_G=2.7\Omega$, $I_D=60A$	---	24.6	---	ns
T_r	Rise Time		---	111.1	---	
$T_{d(off)}$	Turn-Off Delay Time		---	58.3	---	
T_f	Fall Time		---	109.5	---	
C_{iss}	Input Capacitance	$V_{DS}=75V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4930	---	pF
C_{oss}	Output Capacitance		---	722	---	
C_{rss}	Reverse Transfer Capacitance		---	21	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	180	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=60A$, $T_J=25^\circ\text{C}$	---	---	1.4	V
t_{rr}	Reverse Recovery Time	$I_F=90A$, $di/dt=100A/\mu s$	---	97.9	---	nS
Q_{rr}	Reverse Recovery Charge	μs , $T_J=25^\circ\text{C}$	---	326.0	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$
2. The EAS data shows Max. rating . The test condition is $V_{DD}=75V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=68A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Performance Characteristics

Fig 1: Output Characteristics

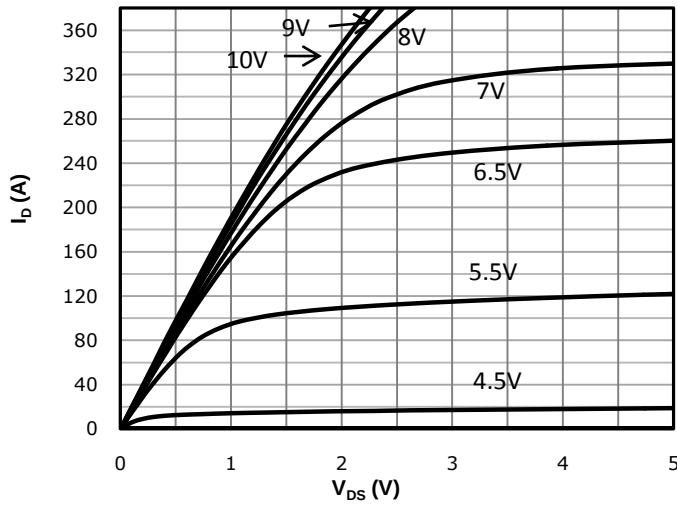


Fig 2: Transfer Characteristics

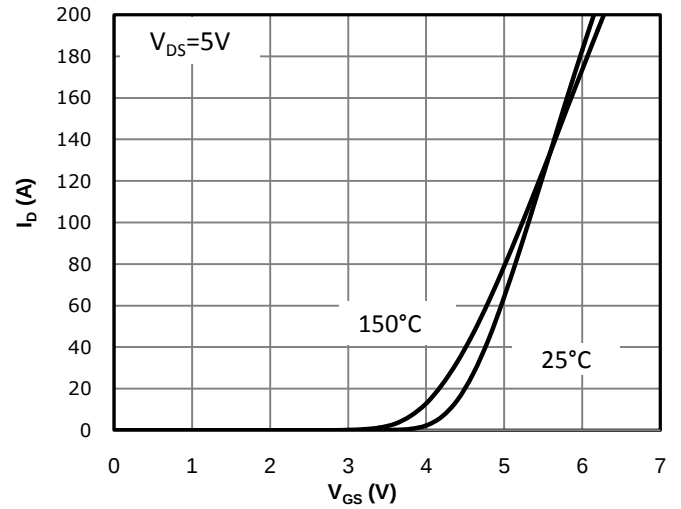


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

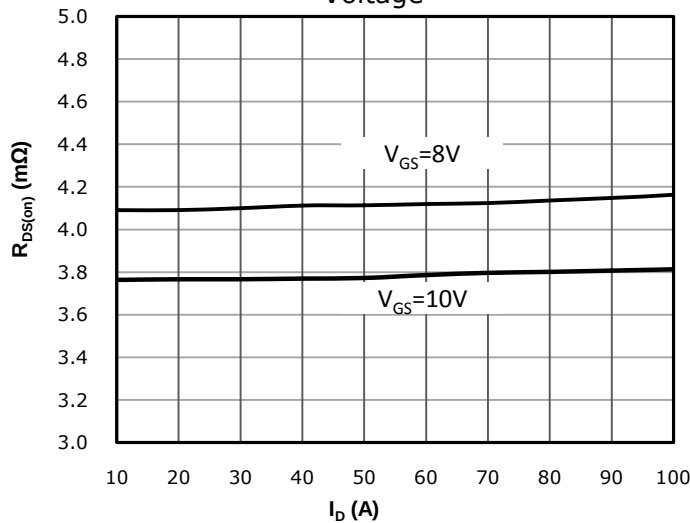


Fig 4: $R_{DS(on)}$ vs Gate Voltage

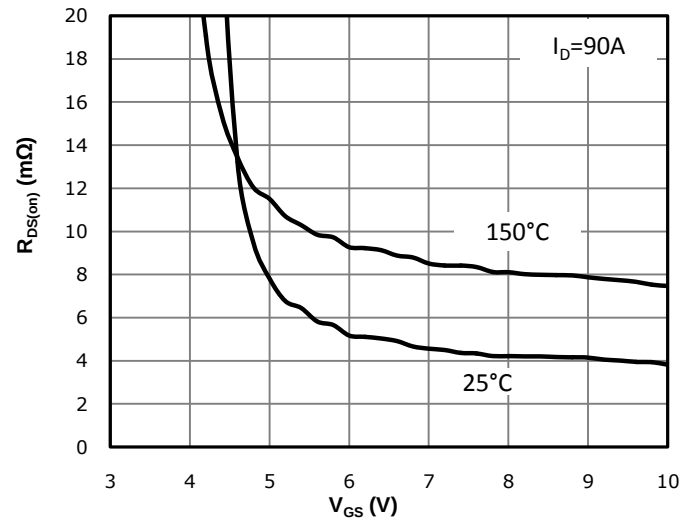


Fig 5: $R_{DS(on)}$ vs. Temperature

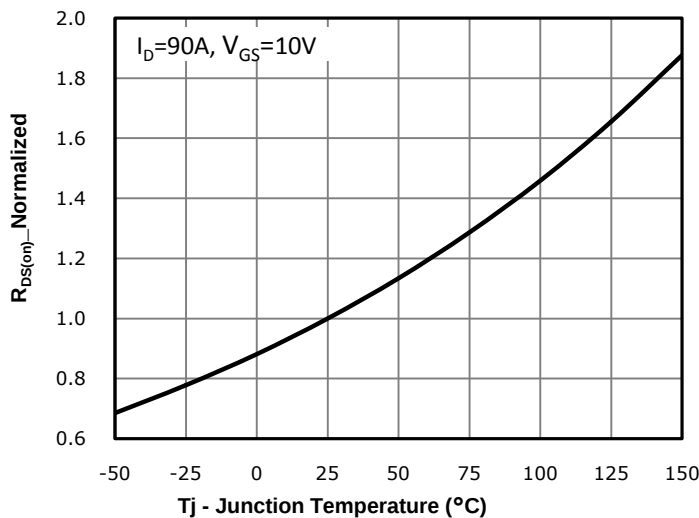


Fig 6: $V_{GS(th)}$ vs. Temperature

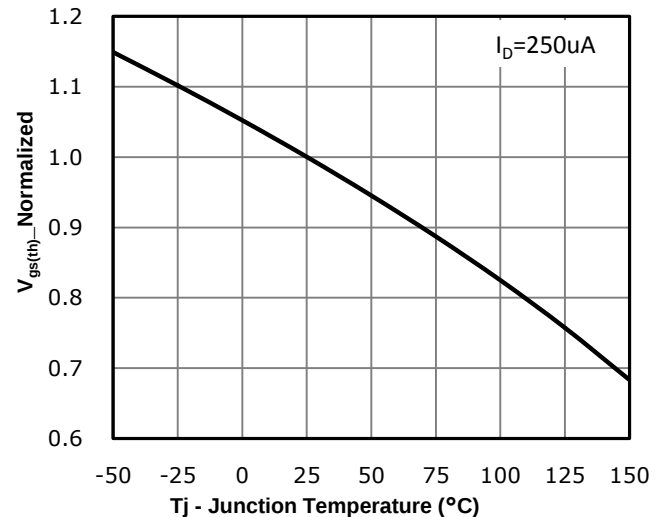


Fig 7: BVdss vs. Temperature

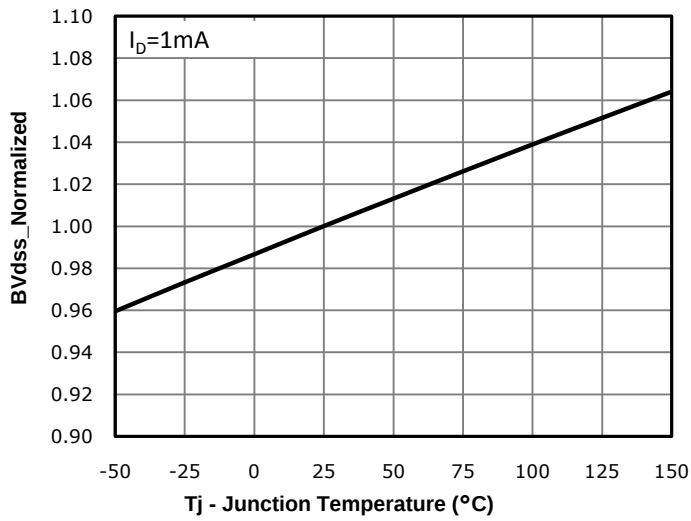


Fig 8: Capacitance Characteristics

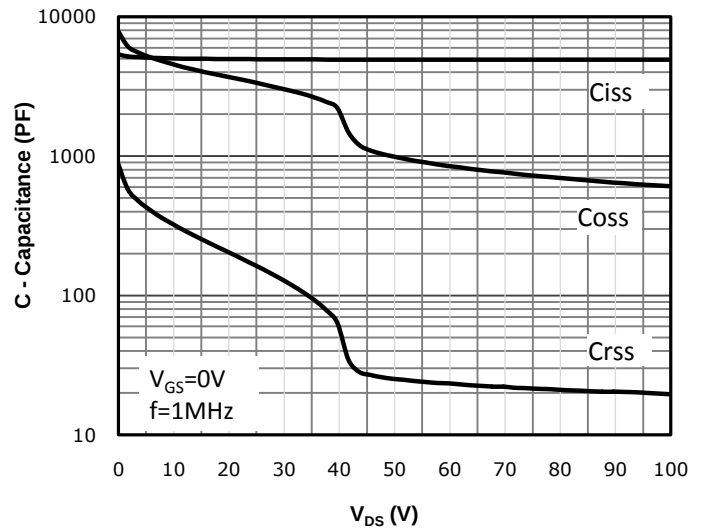


Fig 9: Gate Charge Characteristics

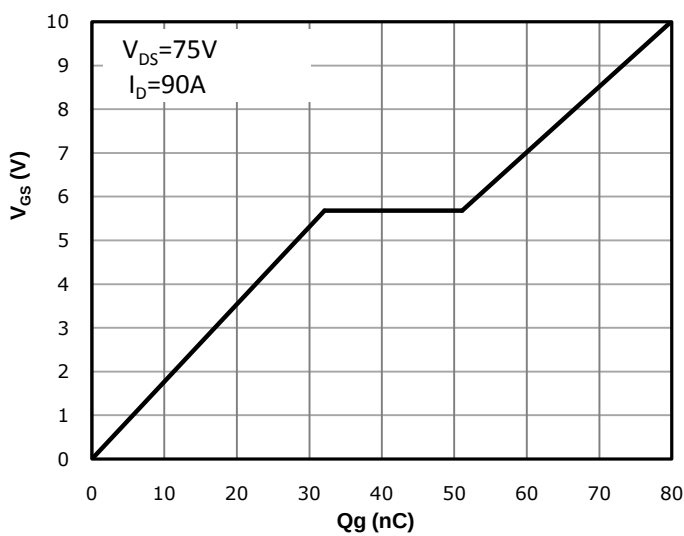


Fig 10: Body-diode Forward Characteristics

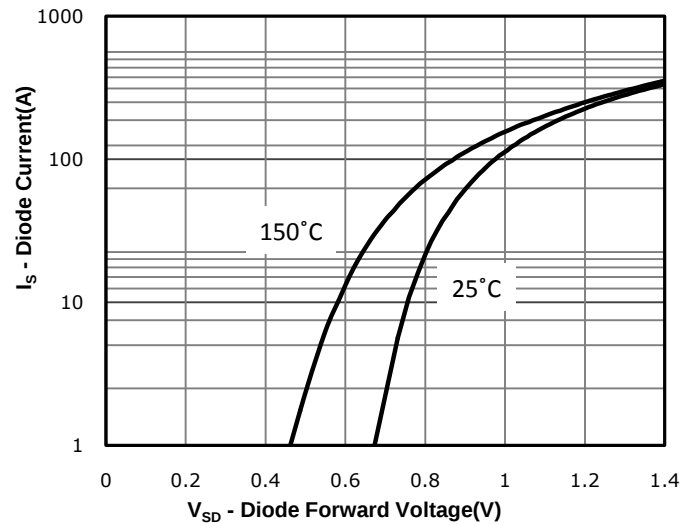


Fig 11: Power Dissipation

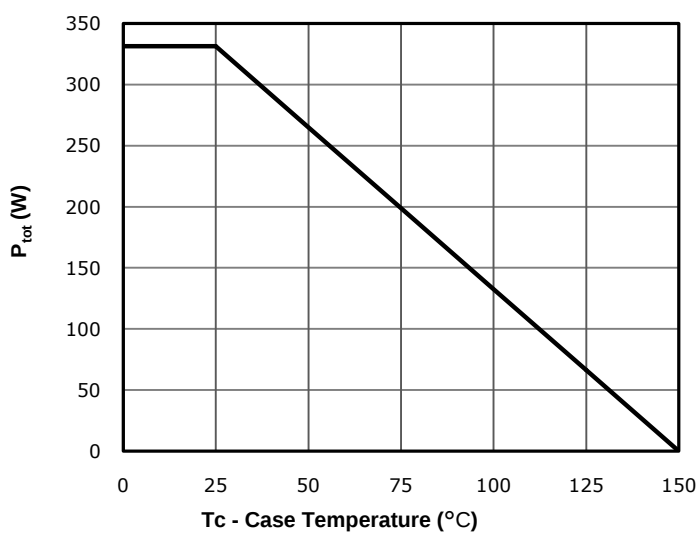


Fig 12: Drain Current Derating

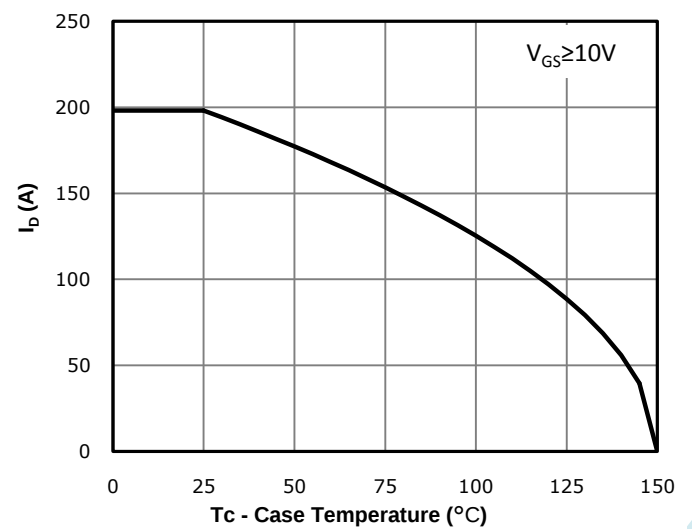


Fig 13: Safe Operating Area

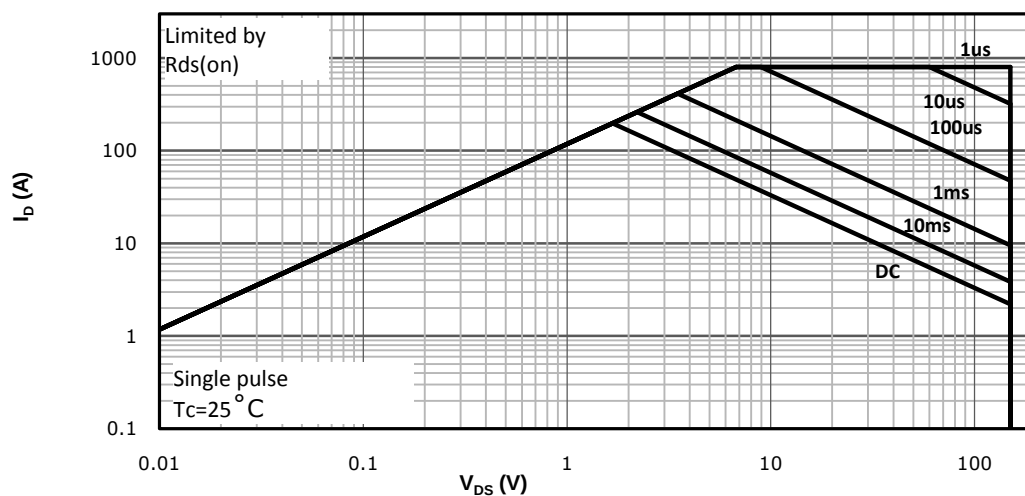
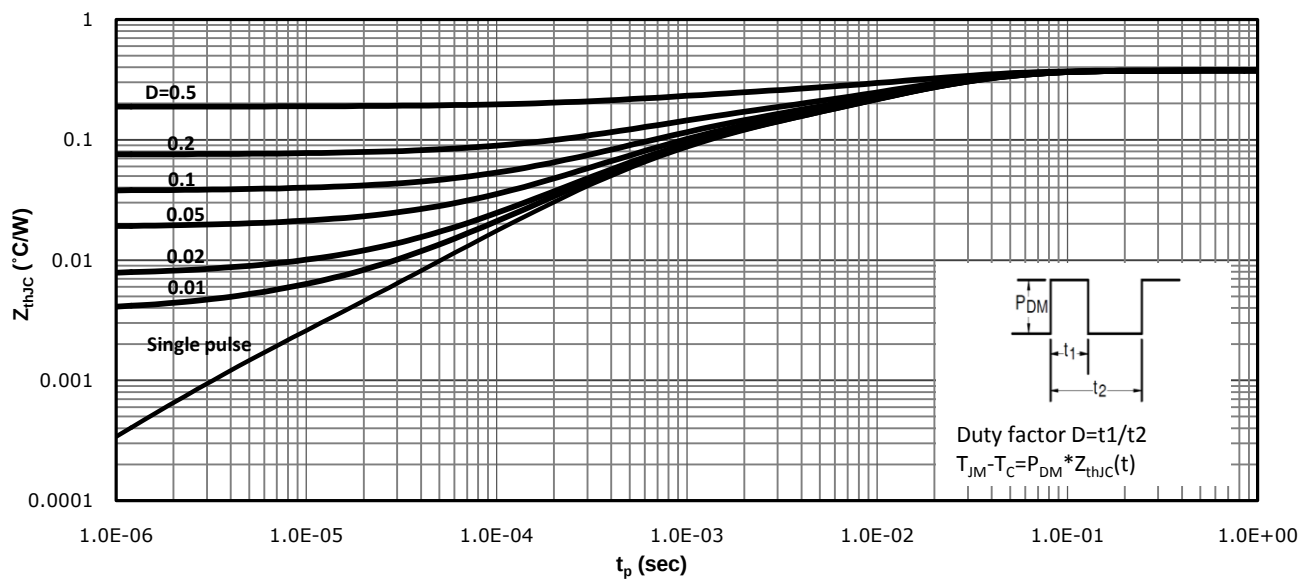
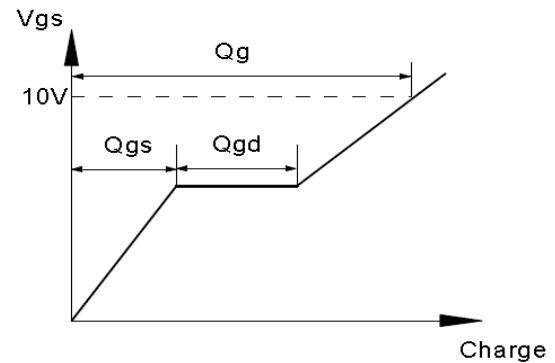
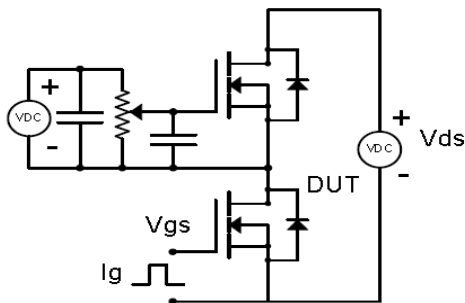


Fig 14: Max. Transient Thermal Impedance

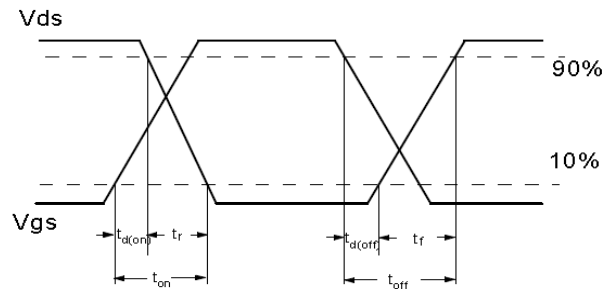
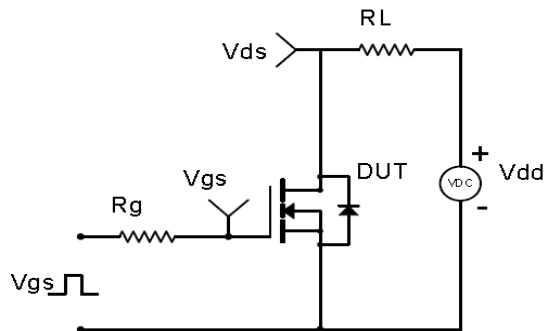


Test Circuit & Waveform

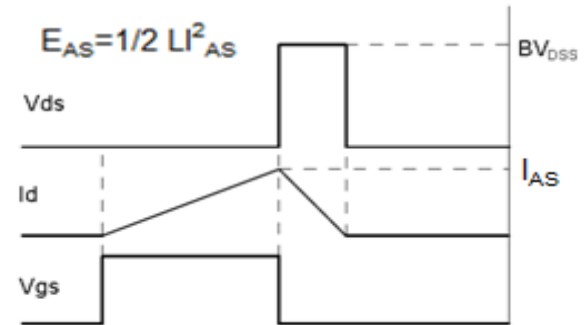
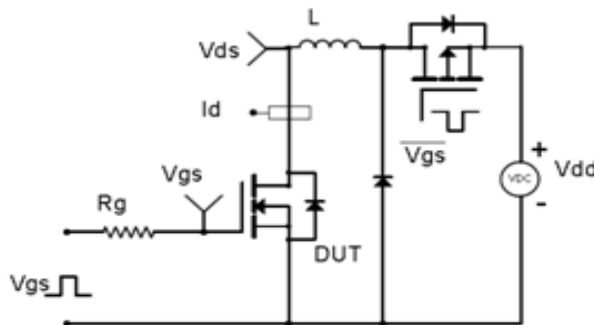
Gate Charge Test Circuit & Waveform



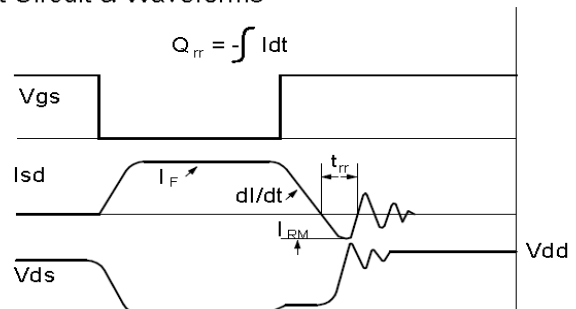
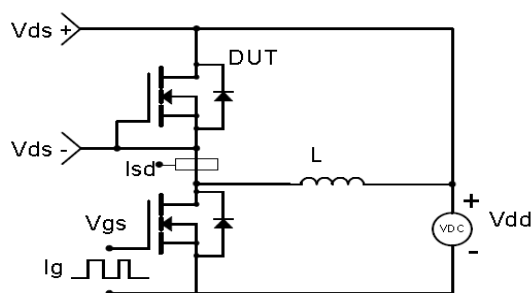
Resistive Switching Test Circuit & Waveforms



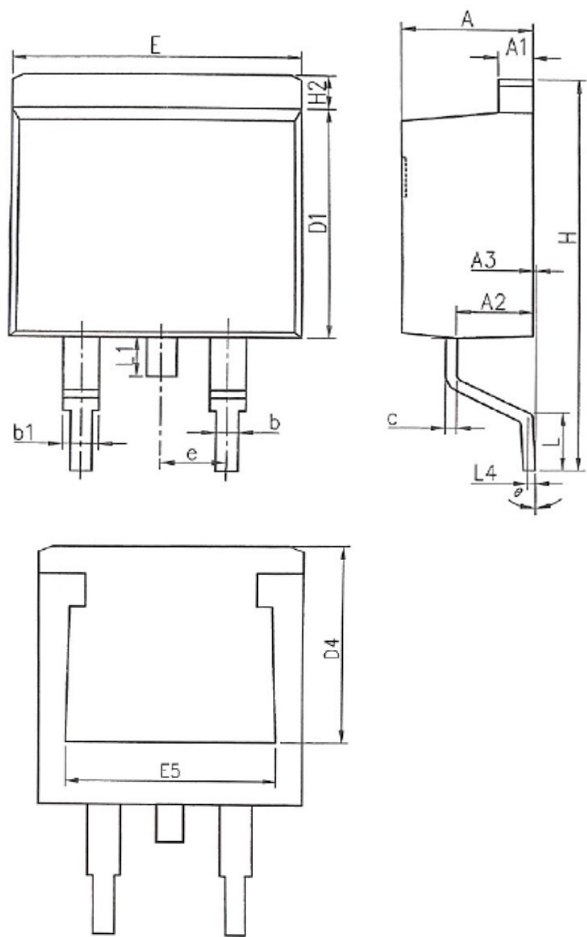
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°